

INCHANGE Semiconductor

isc Product Specification

isc Silicon NPN Darlington Power Transistor

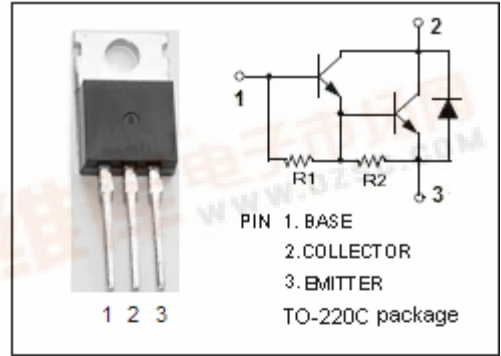
BU920T

DESCRIPTION

- High Voltage
- DARLINGTON

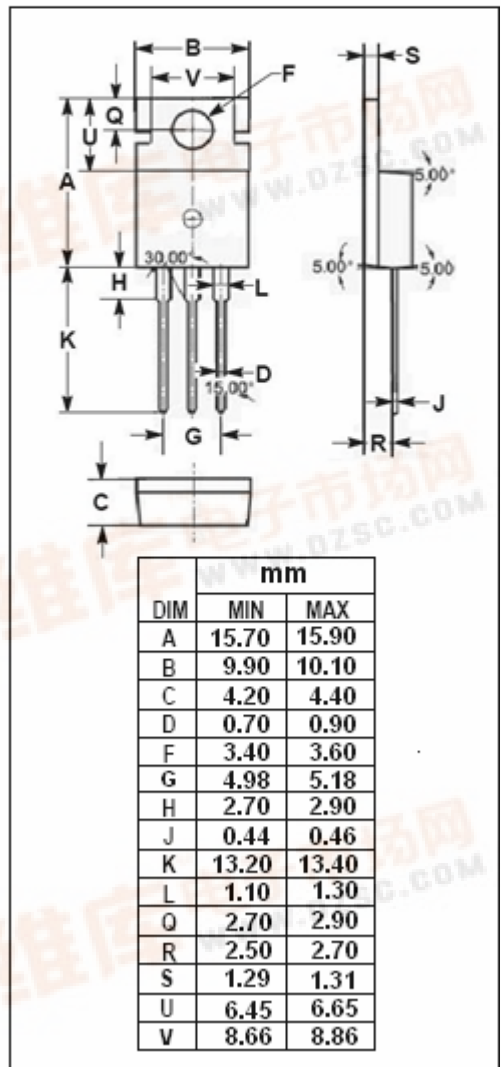
APPLICATIONS

- Designed for automotive ignition applications and inverter circuits for motor control.



ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CES}	Collector-Emitter Voltage V _{BE} = 0	400	V
V _{CEO}	Collector-Emitter Voltage	350	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	10	A
I _{CM}	Collector Current-peak	15	A
I _B	Base Current	5	A
P _C	Collector Power Dissipation @T _C =25°C	105	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.2	°C/W



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.1\text{A}; I_B=0$	350			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=50\text{mA}$			1.8	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=7\text{A}; I_B=140\text{mA}$			1.8	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=50\text{mA}$			2.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C=7\text{A}; I_B=140\text{mA}$			2.5	V
I_{CES}	Collector Cutoff Current	$V_{CE}=400\text{V}; V_{BE}=0$ $V_{CE}=400\text{V}; V_{BE}=0; T_j=125^{\circ}\text{C}$			0.25 0.5	mA
I_{CEO}	Collector Cutoff Current	$V_{CE}=350\text{V}; I_B=0$			0.25	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			50	mA
V_{ECF}	C-E Diode Forward Voltage	$I_F=7\text{A}$			2.5	V